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TIP132 TIP135 TIP137

COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPES

APPLICATION

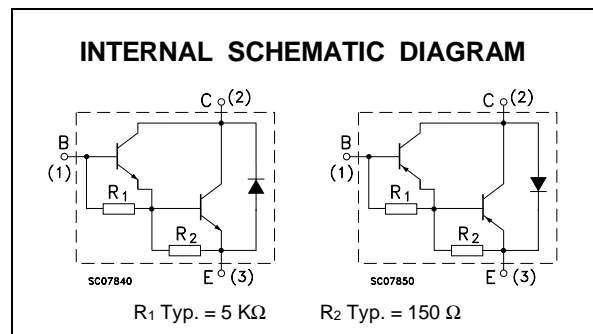
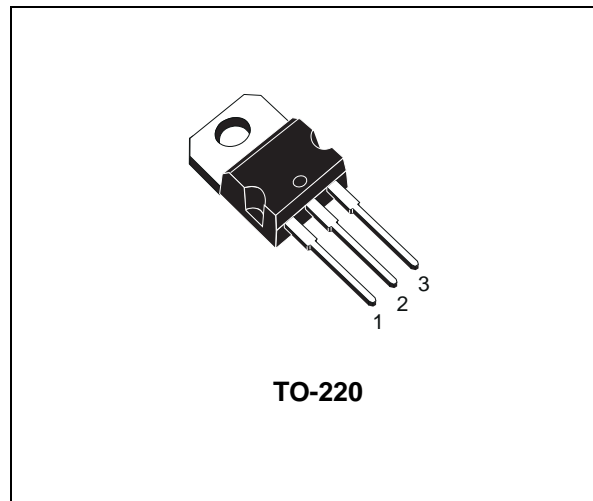
- LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT

DESCRIPTION

The TIP132 is a silicon Epitaxial-Base NPN power transistor in monolithic Darlington configuration, mounted in Jedec TO-220 plastic package. It is intended for use in power linear and switching applications.

The complementary PNP type is TIP137 .

Also TIP135 is a PNP type.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		NPN	TIP132	
		PNP	TIP135	
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	60	100	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	60	100	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	5		V
I_C	Collector Current	8		A
I_{CM}	Collector Peak Current	12		A
I_B	Base Current	0.3		A
P_{tot}	Total Dissipation at $T_{case} \leq 25^\circ C$ $T_{amb} \leq 25^\circ C$	70		W
		2		W
T_{stg}	Storage Temperature	-65 to 150		$^\circ C$
T_j	Max. Operating Junction Temperature	150		$^\circ C$

* For PNP types voltage and current values are negative.

TIP132 / TIP135 / TIP137

THERMAL DATA

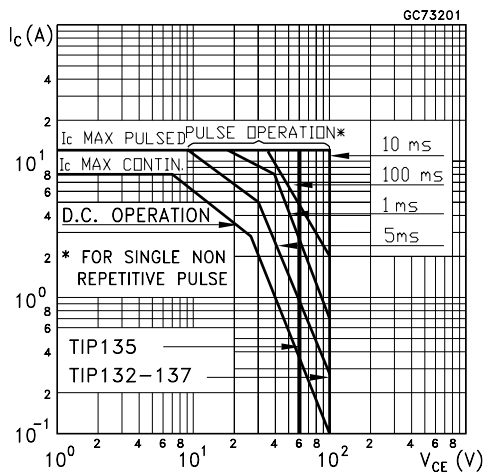
R _{thj-case}	Thermal Resistance Junction-case	Max	1.78	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	63.5	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

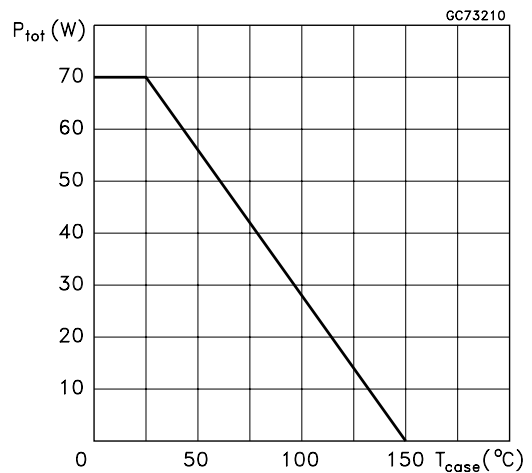
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = Half Rated V _{CEO}			0.5	mA
I _{CBO}	Collector Cut-off Current (I _E = 0)	V _{CB} = Rated V _{CBO}			0.2	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			5	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA for TIP135 for TIP132/TIP137	60 100			V V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 4 A I _B = 16 mA I _C = 6 A I _B = 30 mA			2 4	V V
V _{BE} *	Base-Emitter Voltage	I _C = 4 A V _{CE} = 4 V			2.5	V
h _{FE} *	DC Current Gain	I _C = 1 A V _{CE} = 4 V I _C = 4 A V _{CE} = 4 V	500 1000		15000	

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %
For PNP types voltage and current values are negative.

Safe Operating Areas

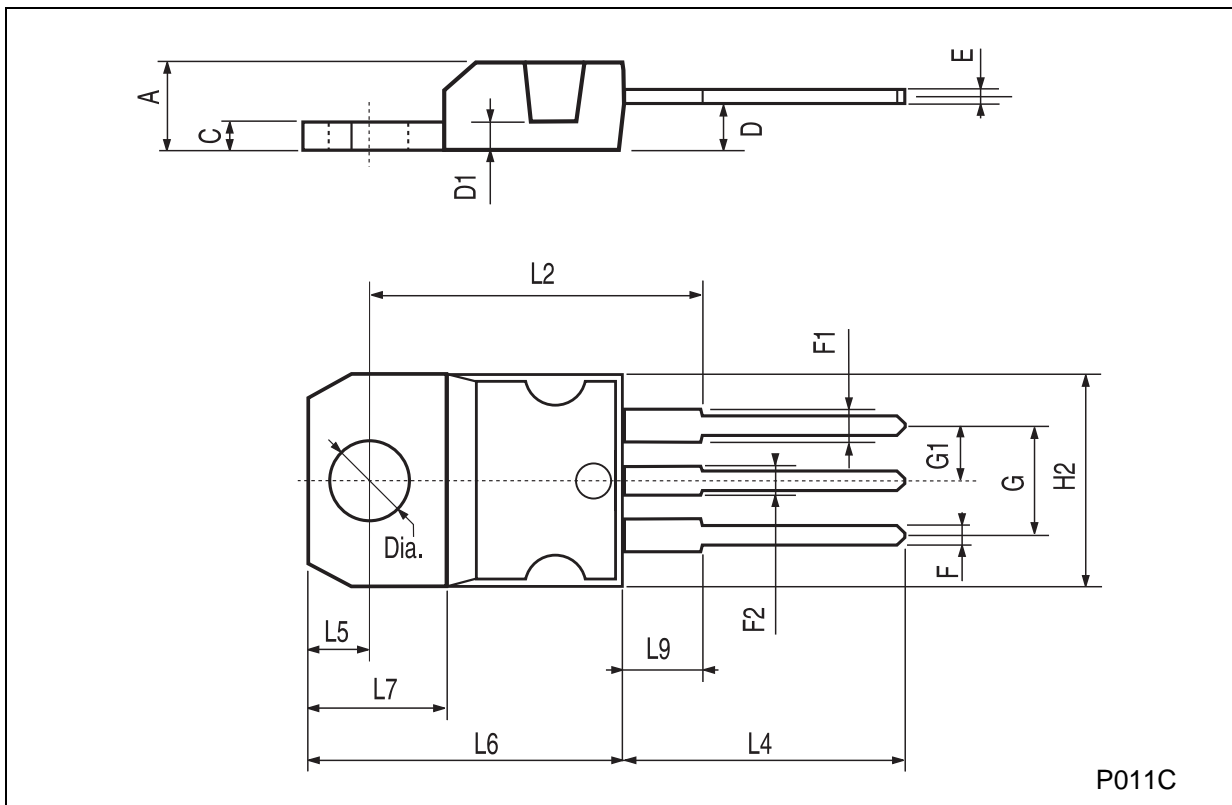


Power Derating Curve



TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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